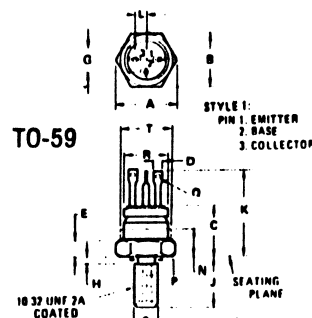


2N5112 PNP Silicon Power Transistor



ABSOLUTE MAXIMUM RATINGS AT 25°C (unless otherwise noted)

	Value	UNITS
Collector — Base Voltage	— 80	Volts
Collector — Emitter Voltage	— 80	Volts
Emitter — Base Voltage	— 10	Volts
Collector Current, Continuous	— 1	Amp
Base Current, Continuous	— 0.5	Amps
Collector Power Dissipation At 25°C Case Temperature	34	Watts
Operating Collector Junction Temperature	175	°C
Storage Temperature	— 65 TO 200	°C

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
B	10.77	11.10	0.424	0.437
C	8.13	11.80	0.320	0.469
E	2.29	3.81	0.090	0.150
G	4.70	6.46	0.185	0.254
H	—	1.98	—	0.078
J	10.16	11.56	0.400	0.455
K	14.48	19.38	0.570	0.763
L	2.29	2.79	0.090	0.110
N	—	6.35	—	0.250
P	4.14	4.80	0.163	0.189
Q	1.02	1.65	0.040	0.065
R	8.08	9.65	0.318	0.380
S	4.212	4.310	0.1658	0.1697
T	9.65	11.10	0.380	0.437

All JEDEC dimensions and notes apply
Collector isolated from case.

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Collector-emitter Sustaining Voltage	BV_{CEO} (sus)*	$I_B = 0, I_C = -50\text{mA}$	— 40			Volts
Forward current Transfer Ratio	h_{FE} *	$I_C = -500\text{mA}, V_{CE} = -4\text{V}$	15		60	
Forward current Transfer Ratio	h_{FE} *	$I_C = -1\text{A}, V_{CE} = -4\text{V}$	5	12		
Collector-emitter Saturation Voltage	$V_{CE}(\text{sat})$ *	$I_C = -500\text{mA}, I_B = -50\text{mA}$			— 0.9	Volts
Collector-emitter Saturation Voltage	$V_{CE}(\text{sat})$ *	$I_C = -1\text{A}, I_B = -250\text{mA}$			— 2.0	Volts
Base-emitter Voltage	$V_{BE}(\text{sat})$ *	$I_C = -500\text{mA}, I_B = -50\text{mA}$			— 1.4	Volts
Collector-cutoff Current	$I_{CIX}(125^\circ\text{C})$	$V_{CE} = \frac{1}{2} \text{ rated voltage}, V_{BE} = +1.5\text{V}, T_C = 125^\circ\text{C}$	— 250			μA
Collector-cutoff Current	I_{CIX}	$V_{CE} = \text{rated voltage}, V_{BE} = +1.5\text{V}$	— 75			μA
Emitter-cutoff Current	I_{EBO}	$V_{EB} = -10\text{V}$	— 75			μA
Collector-cutoff Current	I_{CEO}	$I_B = 0, V_{CE} = \frac{1}{2} \text{ rated voltage}$	— 100			μA
Absolute Magnitude of Forward Current Transfer Ratio	h_{fe}	$V_{CE} = -10\text{V}, I_C = -100\text{mA}, f = 1\text{MHz}$	1	3	8	
Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, f = 1\text{MHz}$		160	500	pf

*Pulse Test PW = 300 μs Duty Cycle $\leq$ 2%

